


REMARKS

The present Preliminary Amendment is submitted to delete the multiple dependencies of claims 29 and 37, thereby placing such claims in condition for examination and reducing the required PTO filing fee.

Copies of the amended portion of the claims with changes marked therein is attached and entitled "*Version with Markings to Show Changes Made.*"

Respectfully submitted,

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Version with Markings to
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28. A plasma processing apparatus as defined in Claim 18, wherein the dielectric tube is protruded by 1 to 10mm from a surface of the metal body or the facing electrode.

29. (Amended) A plasma processing apparatus as defined in Claim 27 ~~or 28~~, wherein the dielectric tube is disposed such that it covers an edge of a hole of the metal body or the facing electrode.

30. A plasma processing apparatus as defined in Claim 18, wherein the hole of the dielectric tube is 0.2 to 2mm in diameter.

31. A plasma processing apparatus as defined in Claim 18, wherein the hole of the dielectric tube is 0.4 to 0.8mm in diameter.

32. A plasma processing apparatus as defined in Claim 18, wherein a frequency of high-frequency power applied to the plasma source, the substrate electrode or the facing electrode is 50MHz to 3GHz.

33. A plasma processing apparatus as defined in Claim 24, wherein the dielectric tube is a bolt screwed in a tap given to the metal body or the facing electrode.

34. A plasma processing apparatus as defined in Claim 24, wherein the dielectric tube has a spot facing for screwdriver or wrench on a side of an inner wall of the vacuum chamber for rotating and screwing the dielectric tube in the metal plate or the facing electrode.

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35. A plasma processing apparatus as defined in Claim 24, wherein the dielectric tube is protruded by 0.5 to 20mm from a surface of the metal body or the facing electrode.

36. A plasma processing apparatus as defined in Claim 24, wherein the dielectric tube is protruded by 1 to 10mm from a surface of the metal body or the facing electrode.

37. (Amended) A plasma processing apparatus as defined in Claim ²⁸
~~27 or 28~~, wherein the dielectric tube is disposed such that it covers an edge of a hole of the metal body or the facing electrode.

38. A plasma processing apparatus as defined in Claim 24, wherein the hole of the dielectric tube is 0.2 to 2mm in diameter.

39. A plasma processing apparatus as defined in Claim 24, wherein the hole of the dielectric tube is 0.4 to 0.8mm in diameter.

40. A plasma processing apparatus as defined in Claim 24, wherein a frequency of high-frequency power applied to the plasma source, the substrate electrode or the facing electrode is 50MHz to 3GHz.